

Band switching diode

DAN235E / DAN235U

● **Applications**

High frequency switching

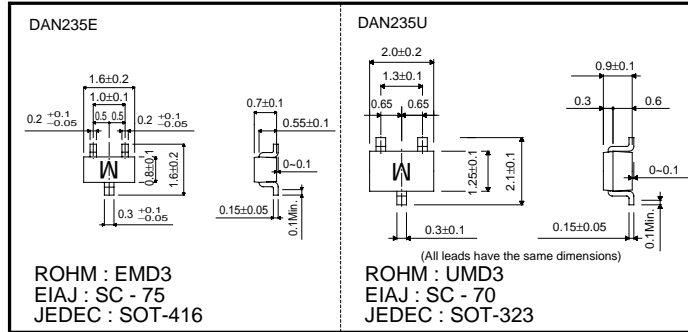
● **Features**

- 1) Small surface mounting type.
(EMD3, UMD3)
- 2) High reliability.

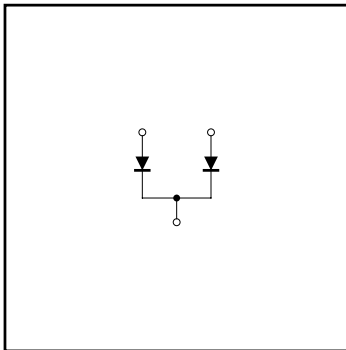
● **Construction**

Silicon epitaxial planar

● **External dimensions (Units : mm)**



● **Circuit**



● **Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	35	V
Power dissipation	P_d	150	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55~+125	°C

Diodes

● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F	–	0.85	1.0	V	I _F =10mA
Reverse current	I _R	–	0.01	10	nA	V _R =25V
Capacitance between terminals	C _T	–	0.87	1.2	pF	V _R =6V, f=1MHz
Forward operating resistance	r _F	–	0.65	0.9	Ω	I _F =2mA, f=100MHz

● Electrical characteristic curves (Ta=25°C)

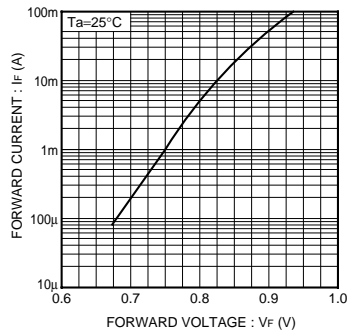


Fig. 1 Forward characteristics

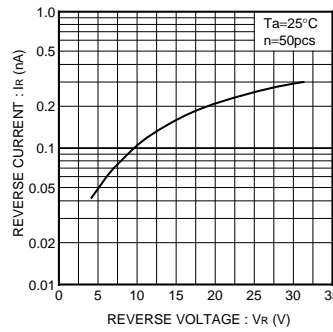


Fig. 2 Reverse characteristics

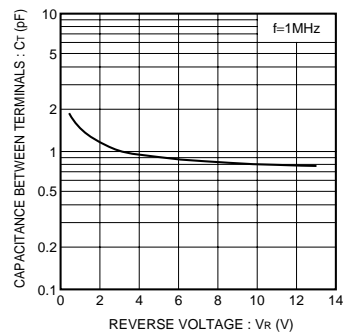


Fig. 3 Capacitance between terminals characteristics

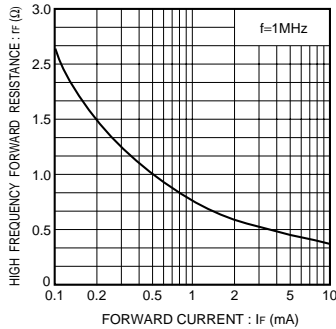


Fig. 4 Forward operating resistance characteristics

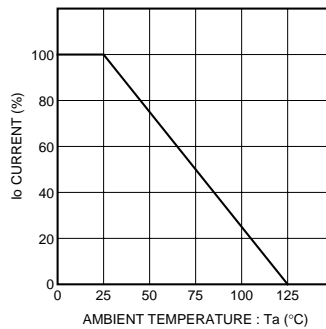


Fig. 5 Derating curve (mounting on glass epoxy PCBs)